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High Performance SWIR HgCdTe 320x256/30 μ m FPAs at Teledyne Judson Technologies

Henry Yuan, Jiawen Zhang, Jongwoo Kim, Carl Meyer, Joyce
Laquindanum, Joe Kimchi, JihFen Lei

221 Commerce Drive, Montgomeryville, PA 18936

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Outline

- **Introduction**
- **Detector and FPA fabrication and Characterization**
- **2.5 μm cutoff FPA performance**
- **2.9 μm cutoff FPA performance**
- **Summary**

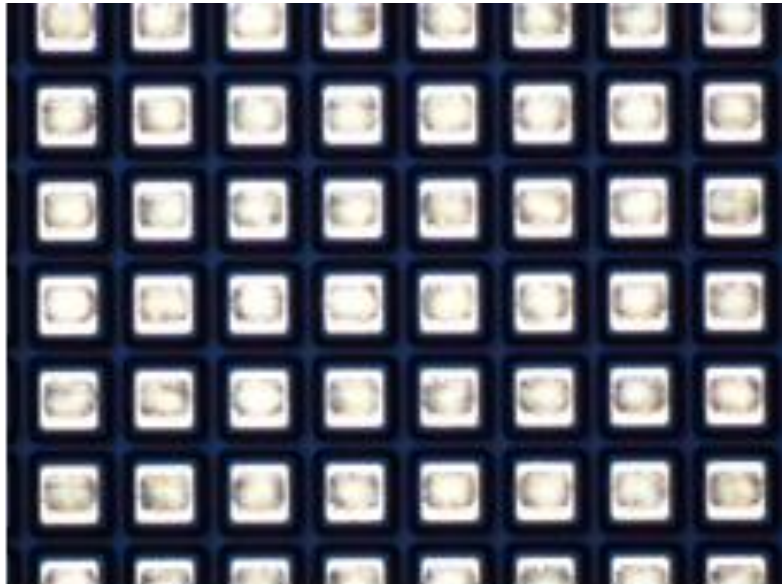
SWIR FPAs, 2-3 μ m Cutoff

- **HgCdTe is still the primary material choice for SWIR FPA at present**
 - Over Ex-InGaAs, SLS/nBn
- **Advanced FPA technologies developed by a number of companies over decades**
 - Large format, small pixel
 - Military applications
 - Space astronomy applications
- **In recent years, increasing demands in**
 - Commercial markets
 - Commercial space applications
- **Requirements**
 - Low cost
 - High operating temperature
 - High performance
 - Small format

320x256/30 μm FPA Fab

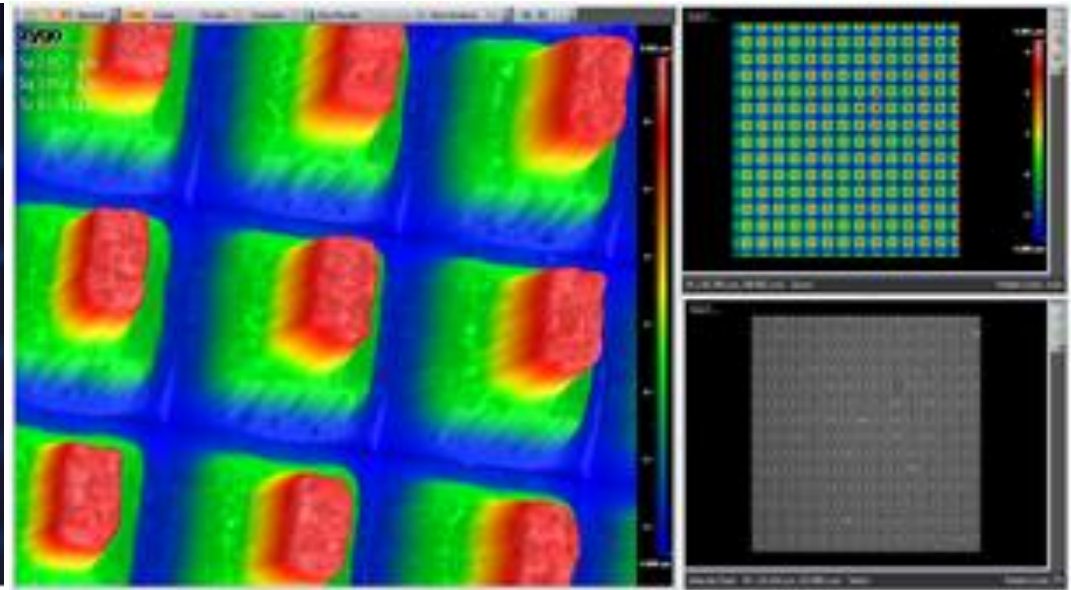
- LPE wafers, as grown P-on-n on CdZnTe, used in early time
- MBE wafers, N-on-n on CZT, As⁺ ion-implantation → P-on-n, grown within Teledyne, used now
- Mesa structure with wet etch
- FLIR ISC9809 ROIC, CTIA input, 2 gains (wells), 170K e⁻ & 3.5M e⁻

Nikon Microscope



In-bumped array, top view

Zygo profilometer



In-bumped array, 3D topography

FPA Characterization

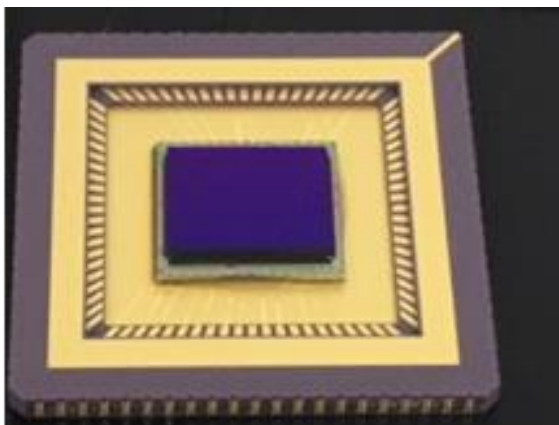
- **2 cutoff wavelengths in general**
 - 2.5 μm and 2.9 μm
- **4 temperatures**
 - $\sim 23^{\circ}\text{C}$, $\sim 5^{\circ}\text{C}$, -70°C , LN_2
- **Detector “dark” current**
 - With and without cold shield
- **NEI (noise equivalent irradiance)**
- **Bad pixel map, operability**
- **IR imaging**
- **Spectral responsivity/QE**
 - On PEC (performance evaluation chip) diodes with backside illumination
- **Pixel capacitance**
 - Measured with a prober (fF limit)
- **Bakeability test**



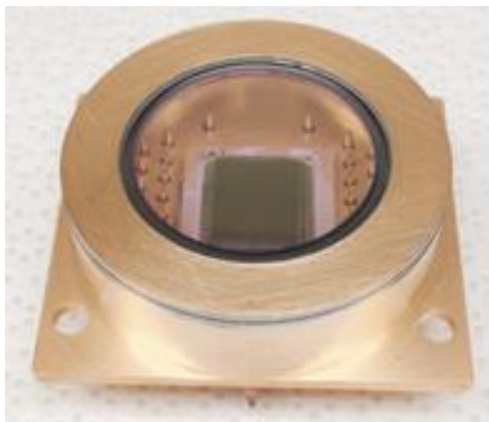
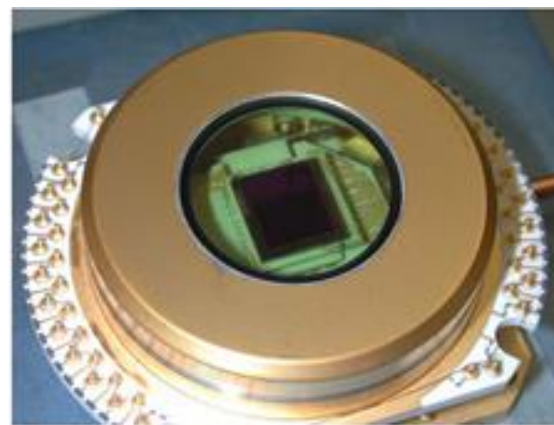
**Integrated lab
camera/dewar**

FPA in Various Packages

84-pin LCC



MC-50 with 4-stage TEC (-85°C)

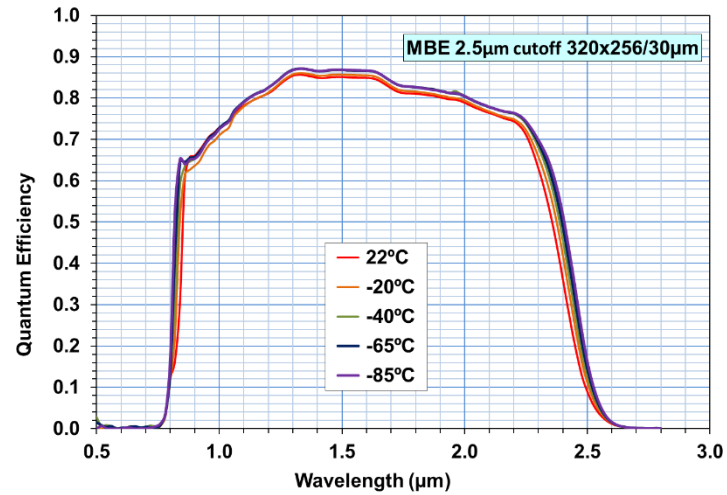
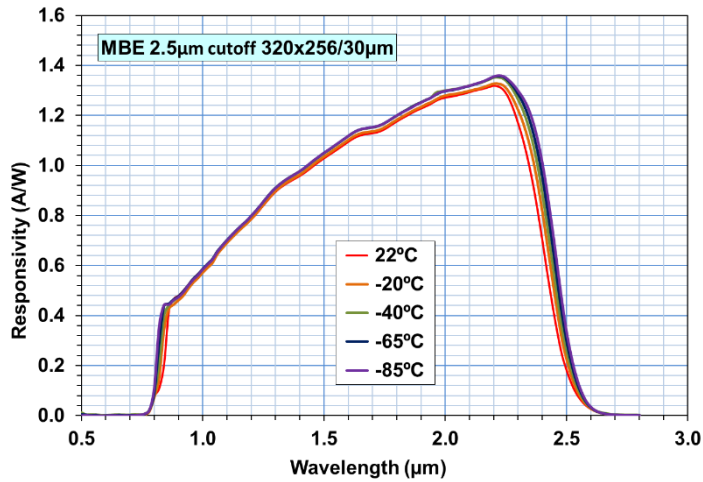


P34DIP with 1-stage TEC (-25°C)

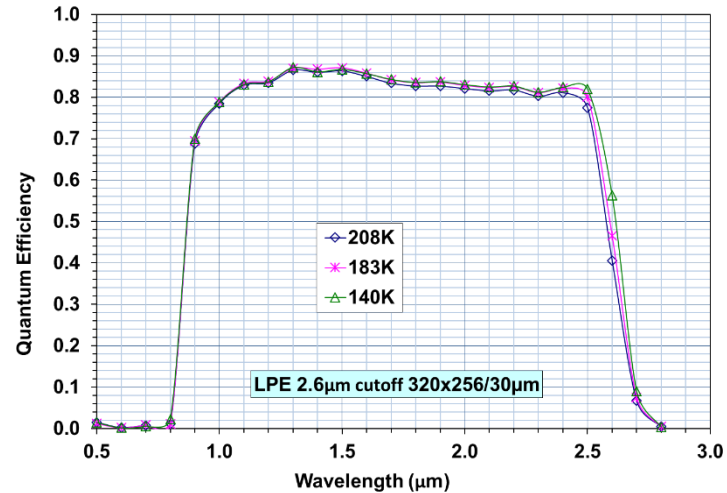
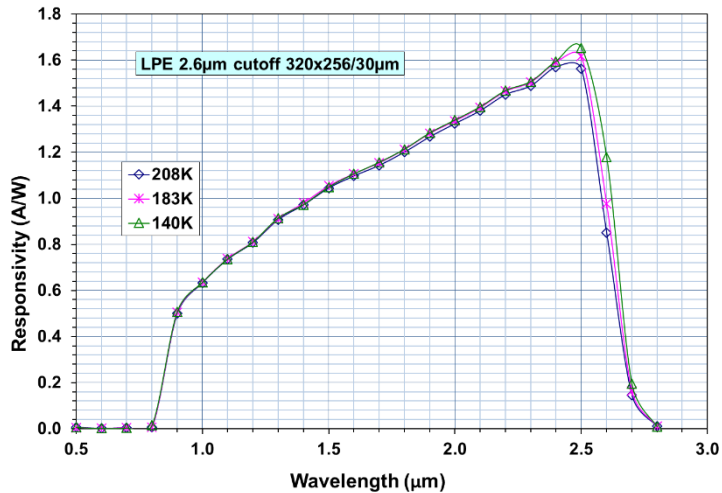


J508 with RICOR micro-cooler (LN₂)

2.5 μm FPAs, Spectral Responsivity & QE



2.45 μm MBE

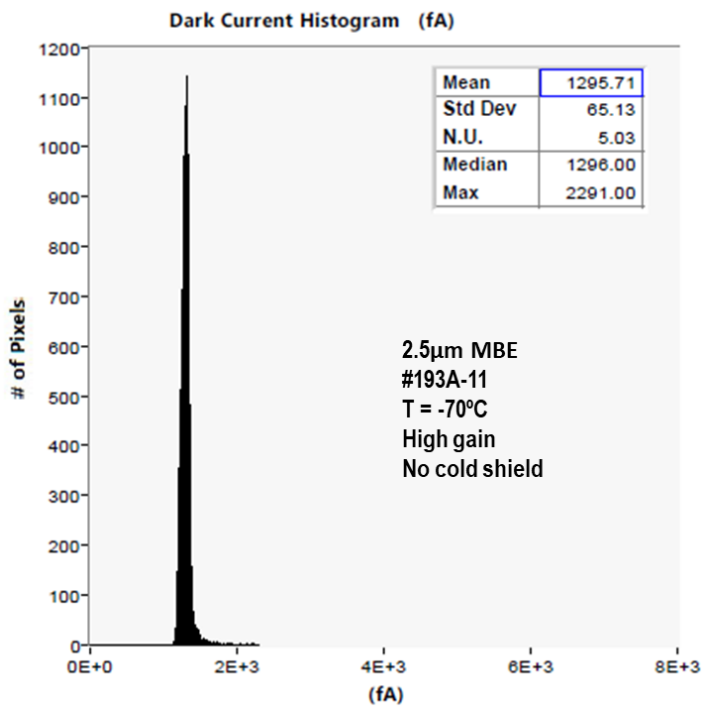


2.6 μm LPE

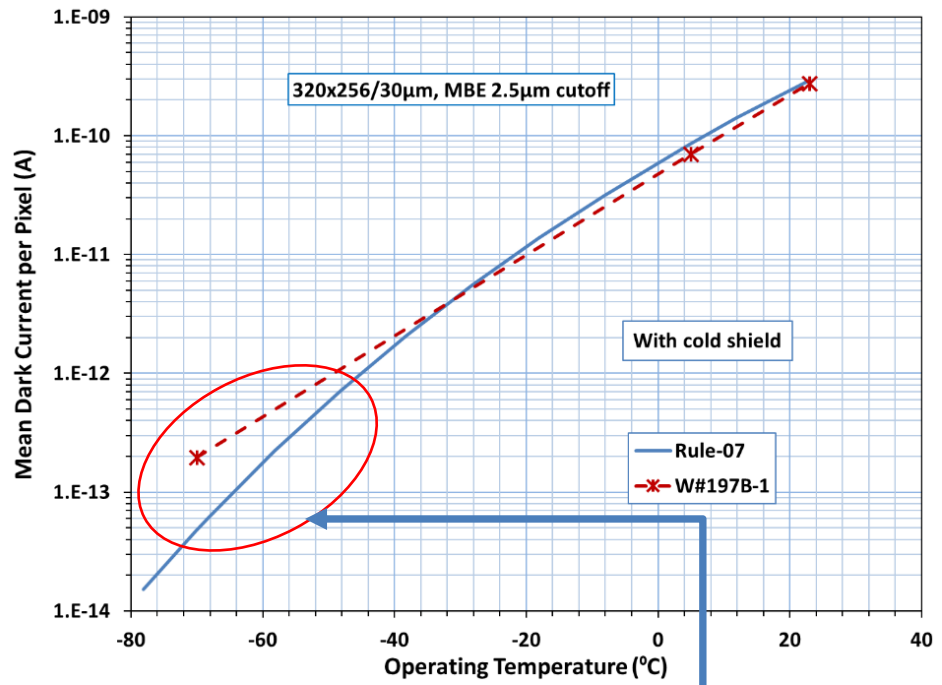
• Peak QE ~85%, single layer ARC

“Dark” Current Histogram and Temperature Dependence

-70°C, no cold shield



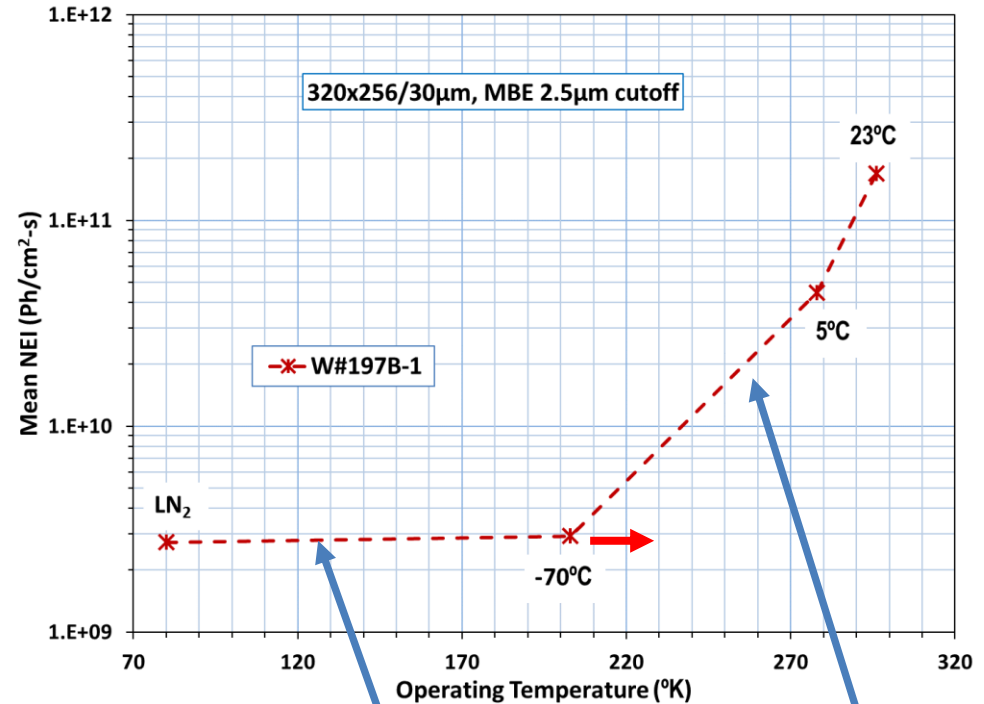
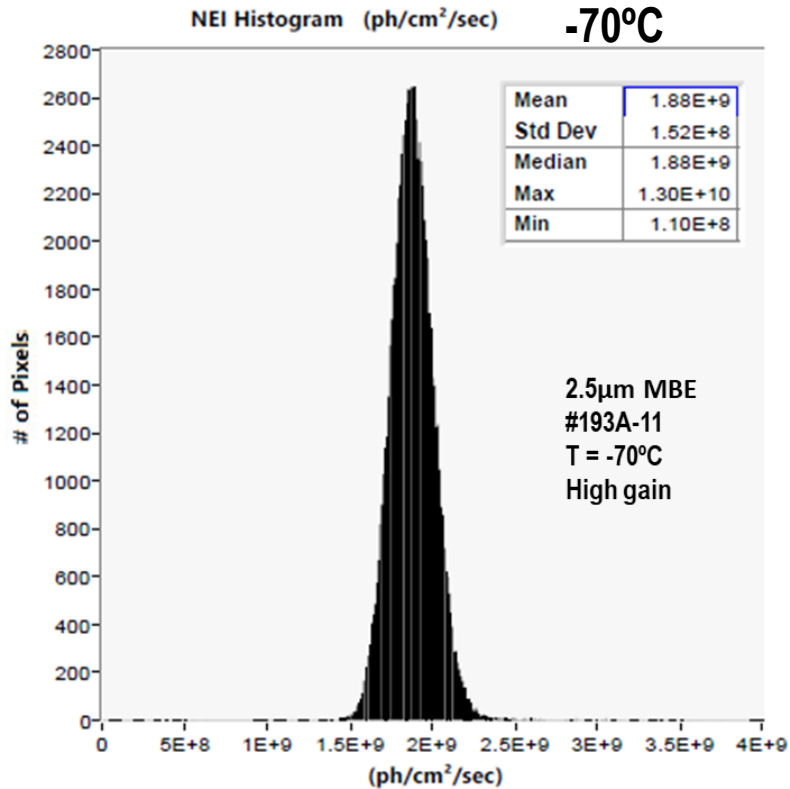
With cold shield



- Background photocurrent dominant at -70°C with FOV ~ 100°, 6.7X higher than dark current (1.3pA vs. 195fA)
- Dark current matches Rule-07 model at high temperatures (> -30°C)
 - Low temperature I_d data affected by background leak and/or camera electronics
- 2.5µm MBE

Background and/or camera limit

NEI Histogram and Temperature Dependence



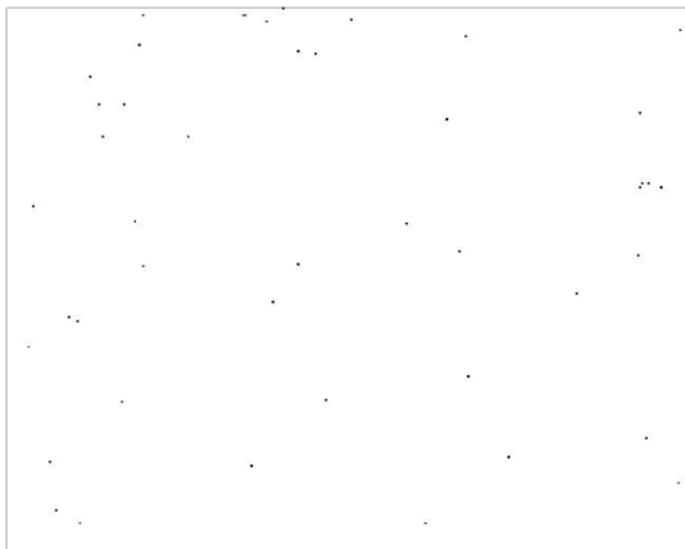
- FOV ~100°, BPF = 1850-2400nm. NEI is background limited near and below -70°C
- NEI = 1.9E9 ph/cm²-s achieved on best unit at -70°C
- Lower NEI could be achieved under smaller FOV, or similar NEI value could be achieved at up to -55°C

Background
limit

Thermal
limit

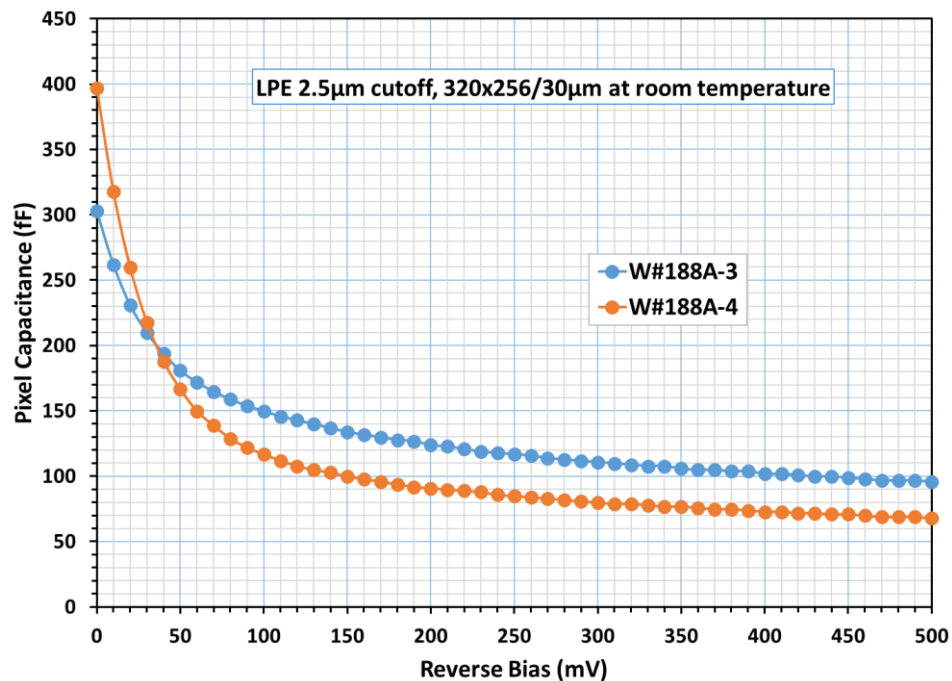
Bad Pixel Map and Pixel Capacitance

-70°C



2.5µm MBE, #193A-11, -70°C, High Gain,
Operability = 99.95%

Room Temperature



- Excellent operability, no bad pixel cluster

- $C_d \sim 100\text{fF}$ at reverse biases

2.5 μ m FPA Imaging at -70 $^{\circ}$ C

Reflective image under bright room light



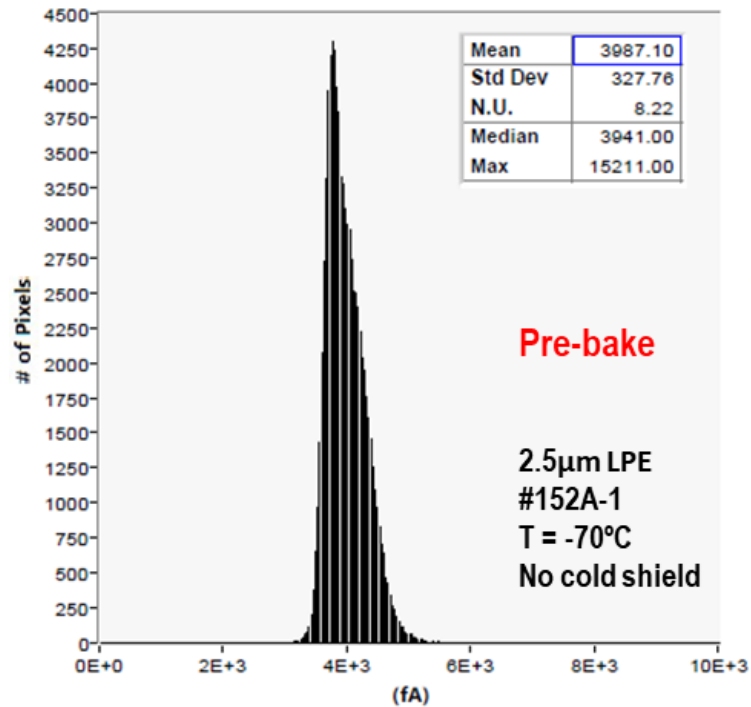
Thermal image in the dark



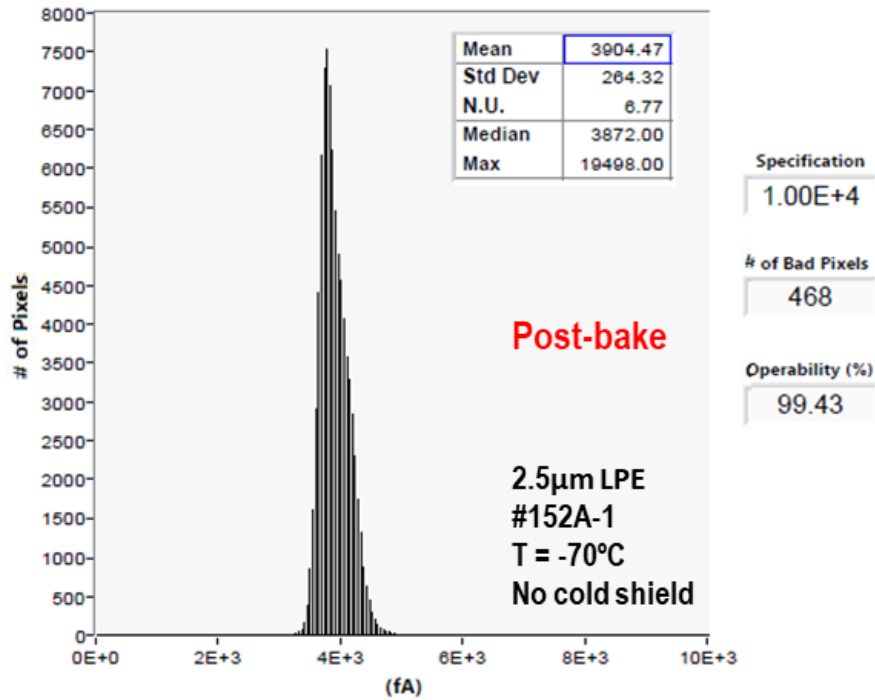
- Similar FPAs, similar camera setup

Bake-ability Test, 136h/80°C in Vacuum Oven

Dark Current Histogram (fA)



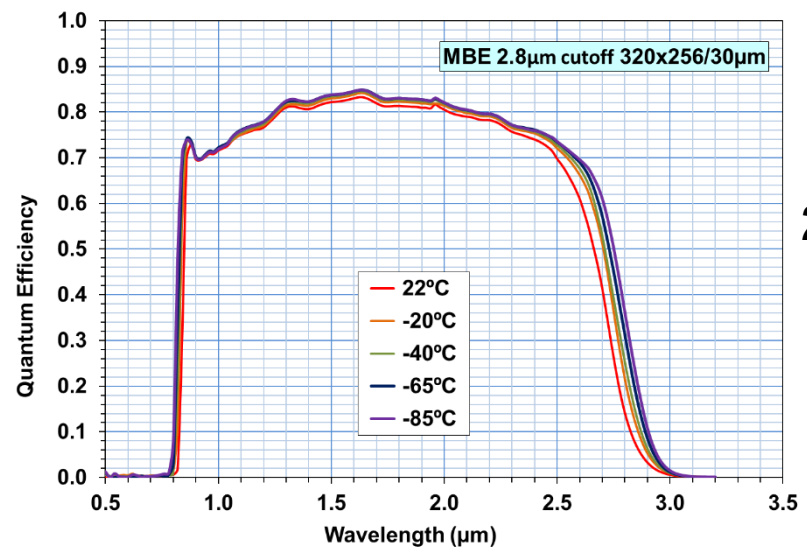
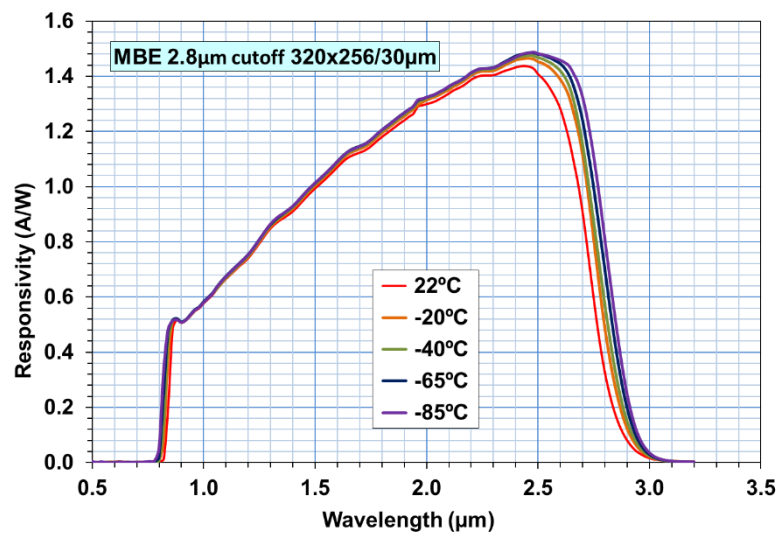
Dark Current Histogram (fA)



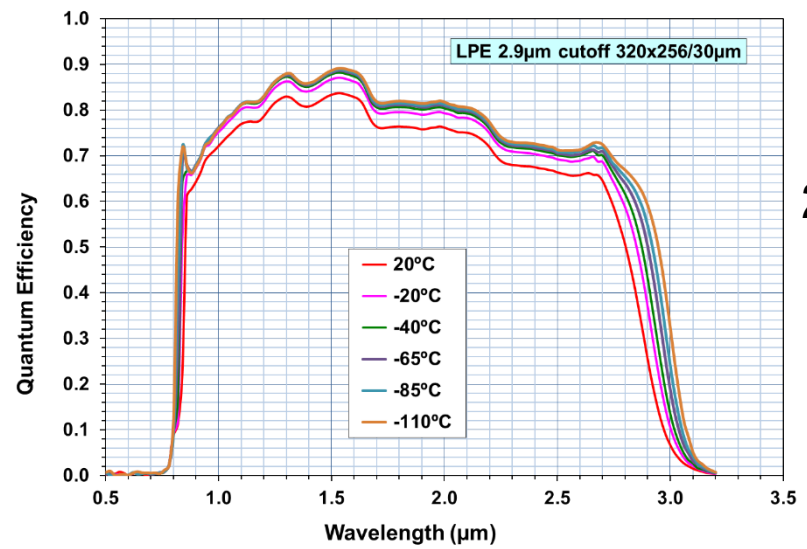
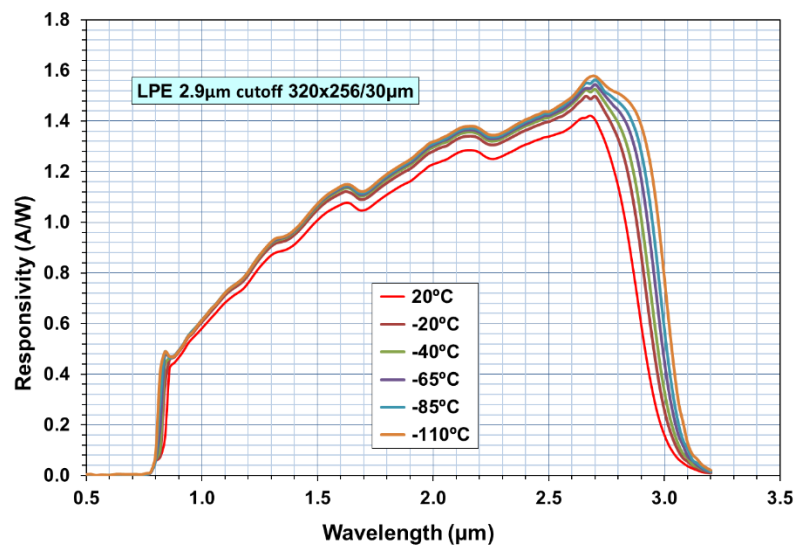
- 2.5µm LPE, -70°C, no cold shield
- Mean I_d : 4.0pA → 3.9pA
- NU: 8.2% → 6.8%
- Bad pixel count: 411 → 468
- Operability: 99.50% → 99.43%

No performance degradation

2.9μm FPAs, Spectral Responsivity & QEAs



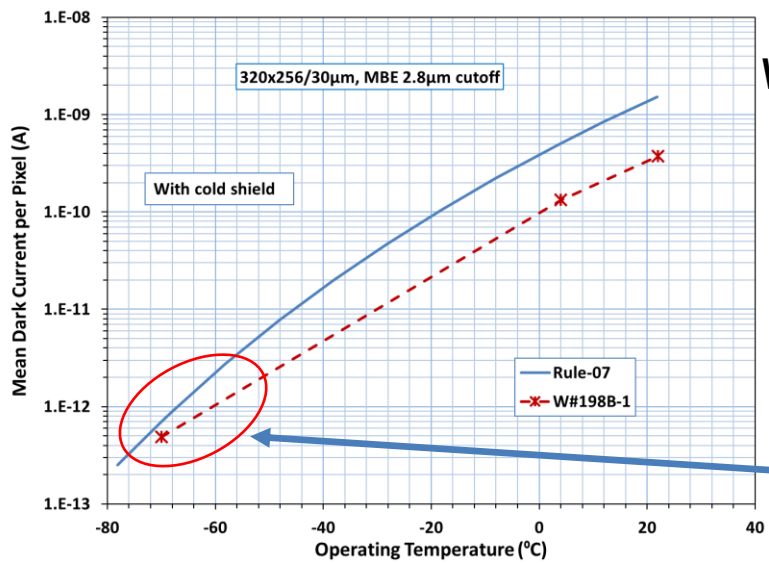
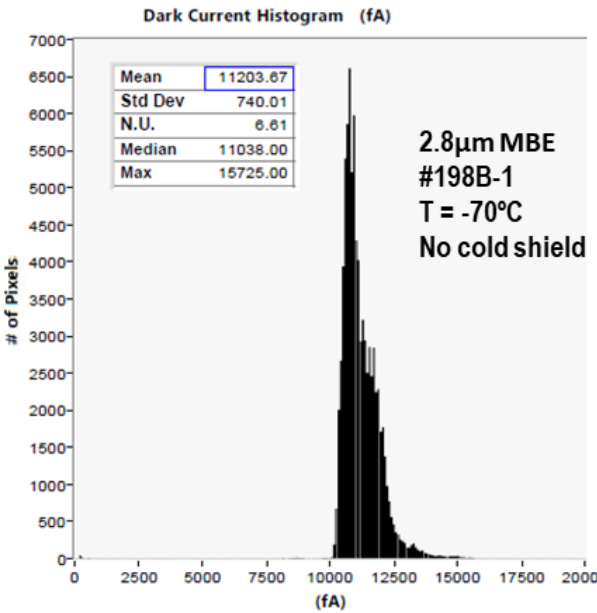
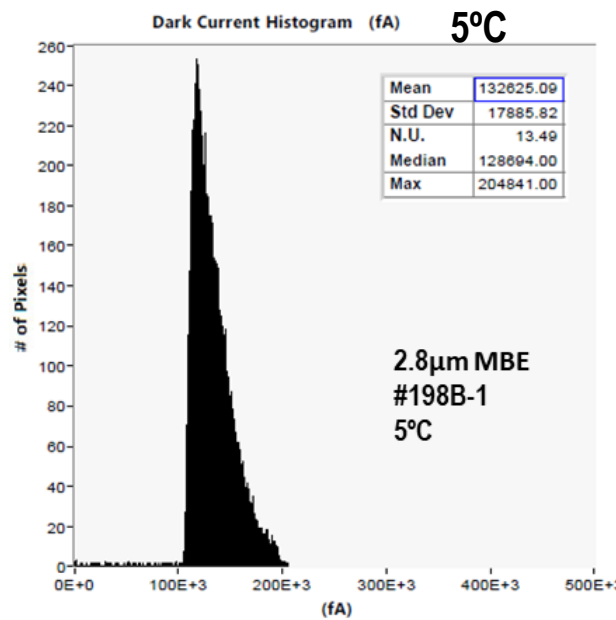
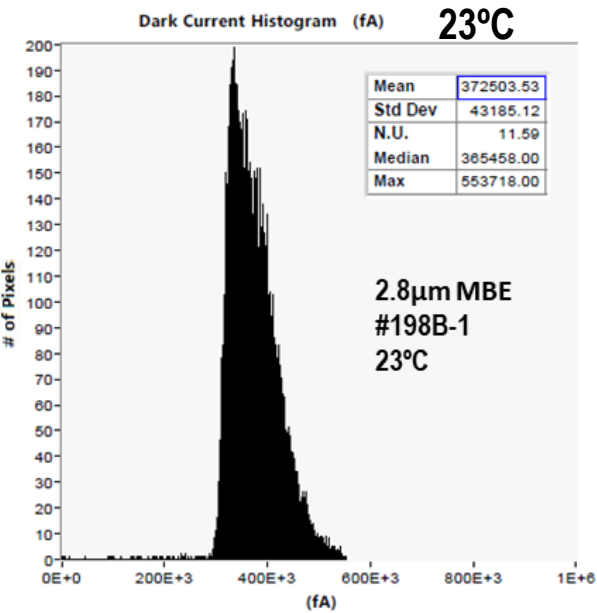
2.8μm MBE



2.9μm LPE

• Peak QE ~85%, single layer ARC

“Dark” Current Histogram and Temperature Dependence



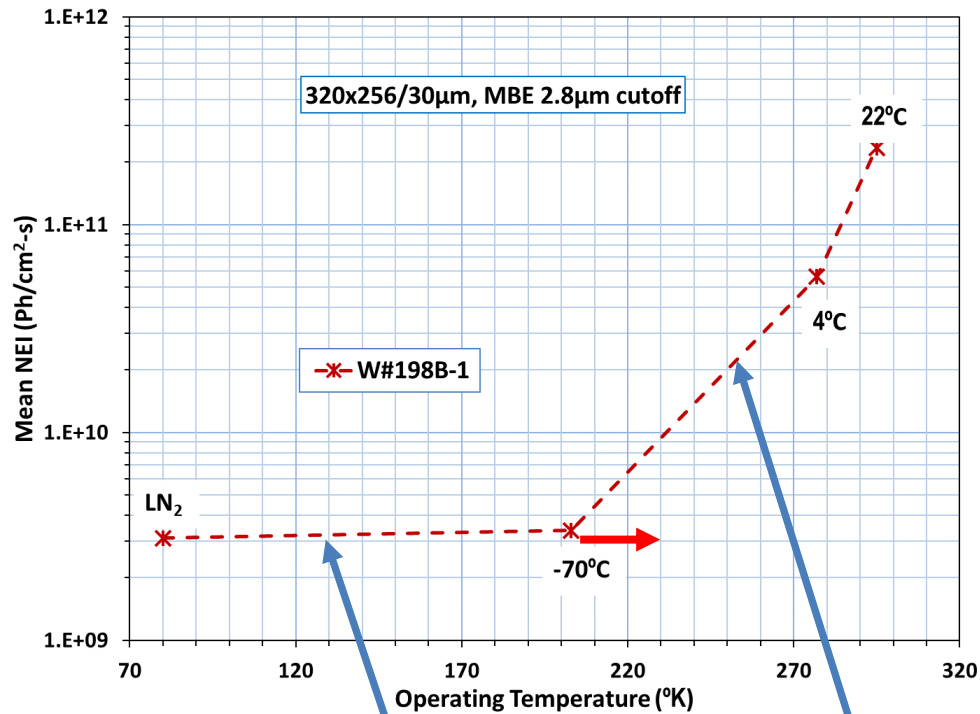
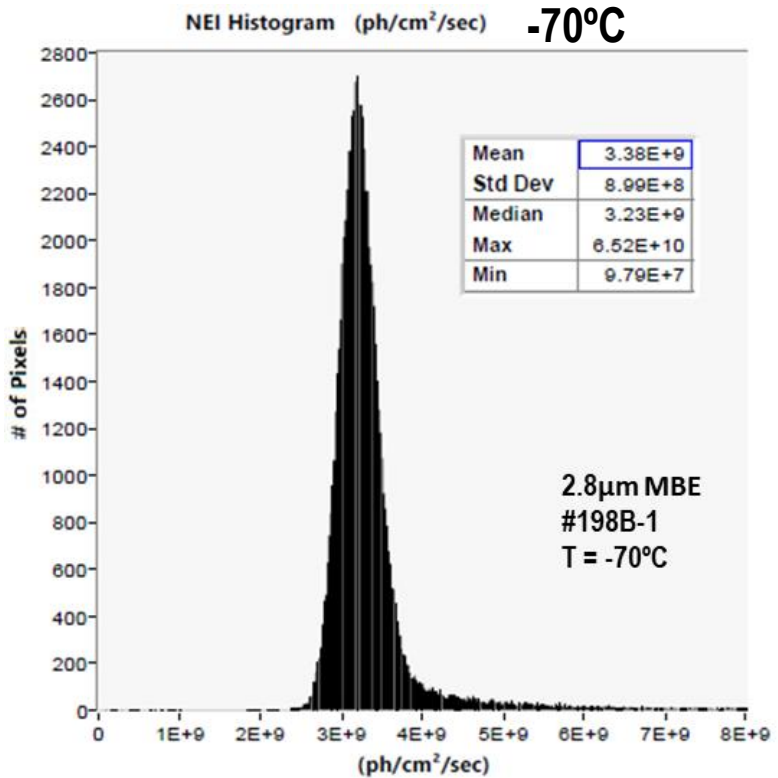
- Background photocurrent dominant at -70°C with FOV ~ 100°, 23X higher than dark current (11.2pA vs. 487fA)
- Dark current ~4X lower than Rule-07 model at high temperatures (> -30°C)
 - Low temperature I_d data affected by background leak and/or camera electronics

• 2.8µm MBE

With cold shield

Background and/or camera limit

NEI Histogram and Temperature Dependence



- FOV ~100°, BPF = 1850-2400nm. NEI is background limited near and below -70°C
- Typical NEI = 3.4E9 ph/cm²-s at -70°C
- Lower NEI could be achieved under smaller FOV, or similar NEI value could be achieved at up to -40°C

Background limit

Thermal limit

Bad Pixel Map and Pixel Capacitance

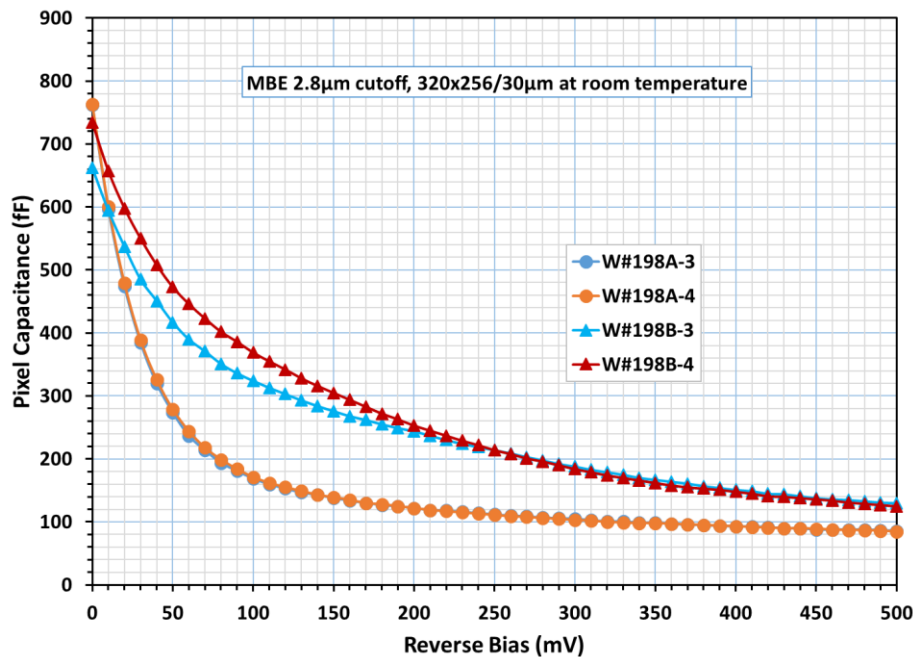
-70°C



2.8µm MBE, #198B-1, -70°C, Low Gain,
Operability = 99.89%

- Excellent operability, no bad pixel cluster

Room Temperature



- $C_d \sim 100\text{-}300\text{fF}$ at reverse biases

2.9 μ m FPA Imaging at -70 $^{\circ}$ C

Reflective image under bright room light



Thermal image in the dark



- Same FPA, same camera setup, taken at same time, looking at same scene

- **Excellent operability and detector yield achieved with state-of-the-art Teledyne MBE materials on CZT and a P-on-n mesa structure based process**
 - 2.5 μm and 2.9 μm cutoff SWIR FPAs
 - Typical operability ~99.9% with few or no bad pixel cluster
 - Low cost production
- **Dark current matches or below Rule-07 at high temperatures ($> -70^\circ\text{C}$)**
 - 275pA and 372pA at room temperature for typical 2.5 μm and 2.9 μm FPAs respectively
 - 195fA and 487fA at -70°C for typical 2.5 μm and 2.9 μm FPAs respectively
- **NEI limited by background at -70°C with FOV $\sim 100^\circ$**
 - 1.9E9 Ph/cm²-s for best 2.5 μm FPA
 - 3.4E9 Ph/cm²-s for typical 2.9 μm FPAs
- **NEI would be even lower under smaller FOV**
 - Similar NEI could be achieved at higher temperatures, up to -55°C for 2.5 μm FPAs and up to -40°C for 2.9 μm FPAs
- **Peak QE $\sim 85\%$ with a single layer AR coating**
- **Pixel capacitance $\sim 100\text{-}300\text{fF}$ at reverse bias of 100-200mV**



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